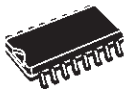
74VHC238

3 TO 8 LINE DECODER

- HIGH SPEED: t_{PD} =5.5 ns (TYP.) at V_{CC} = 5V
- LOW POWER DISSIPATION:
  I_{CC} = 4 µA (MAX.) at T_A = 25 °C
- HIGH NOISE IMMUNITY:
  $V_{NIH} = V_{NIL}$ = 28% V_{CC} (MIN.)
- POWER DOWN PROTECTION ON INPUTS
- SYMMETRICAL OUTPUT IMPEDANCE:
  $|I_{OH}| = I_{OL}$ = 8 mA (MIN)
- BALANCED PROPAGATION DELAYS:
  $t_{PLH} \cong t_{PHL}$
- OPERATING VOLTAGE RANGE:
  V_{CC} (OPR) = 2V to 5.5V
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 238
- IMPROVED LATCH-UP IMMUNITY



M1
(Micro Package)



T
(TSSOP Package)

ORDER CODES :

74VHC238M 74VHC238T

DESCRIPTION

The 74VHC238 is an advanced high-speed CMOS 3 TO 8 LINE DECODER fabricated with sub-micron silicon gate and double-layer metal wiring C^2MOS technology.

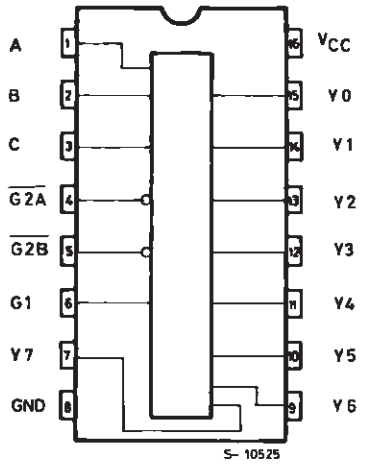
If the device is enabled, 3 binary select inputs (A, B and C) determine which one of the outputs will go high. If enable input G1 is held low or either $\overline{G2A}$ or $\overline{G2B}$ is held high, decoding function is inhibited and all the 8 outputs go to low.

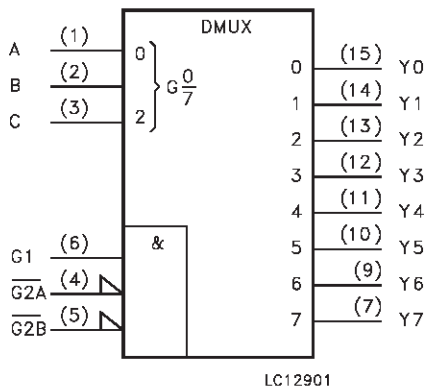
Three enable inputs are provided to ease cascade connection and application of this address decoders for memory systems.

Power down protection is provided on all inputs and 0 to 7V can be accepted on inputs with no regard to the supply voltage. This device can be used to interface 5V to 3V.

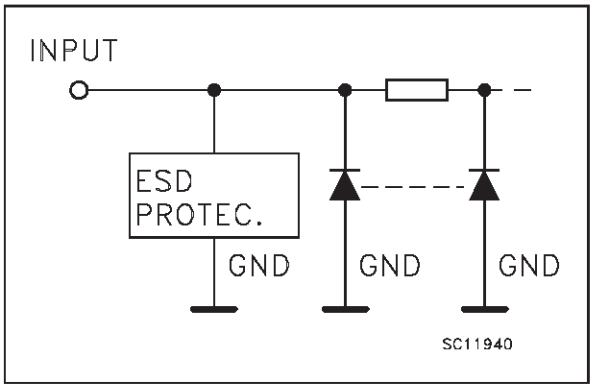
All inputs and outputs are equipped with protection circuits against static discharge, giving them 2KV ESD immunity and transient excess voltage.

PIN CONNECTION AND IEC LOGIC SYMBOLS





INPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

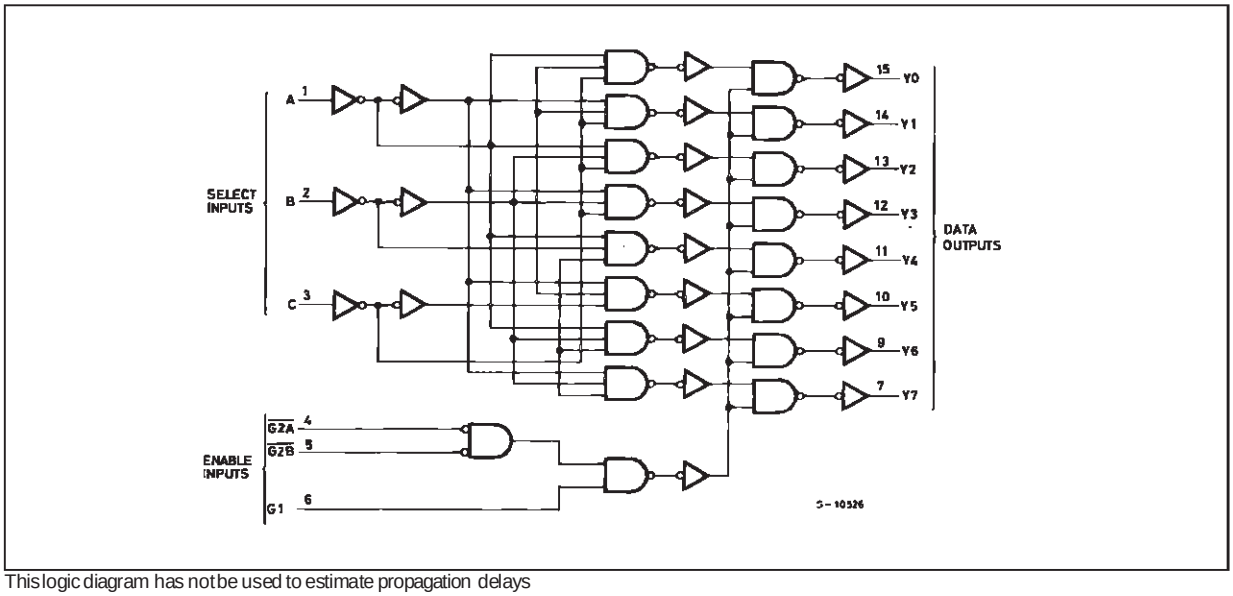
PIN No	SYMBOL	NAME AND FUNCTION
1, 2, 3	A, B, C	Address Inputs
4, 5	$\overline{G2A}$, $\overline{G2B}$	Enable Inputs
6	G1	Enable Input
15, 14, 13, 12, 11, 10, 9, 7	Y0 to Y7	Outputs
8	GND	Ground (0V)
16	V_{CC}	Positive Supply Voltage

TRUTH TABLE

INPUTS						OUTPUTS							
ENABLE			SELECT										
$\overline{G2B}$	$\overline{G2A}$	G1	C	B	A	Y0	Y1	Y2	Y3	Y4	Y5	Y6	Y7
X	X	L	X	X	X	L	L	L	L	L	L	L	L
X	H	X	X	X	X	L	L	L	L	L	L	L	L
H	X	X	X	X	X	L	L	L	L	L	L	L	L
L	L	H	L	L	L	H	L	L	L	L	L	L	L
L	L	H	L	L	H	L	H	L	L	L	L	L	L
L	L	H	L	H	L	L	L	H	L	L	L	L	L
L	L	H	L	H	H	L	L	L	H	L	L	L	L
L	L	H	H	L	L	L	L	L	L	H	L	L	L
L	L	H	H	L	H	L	L	L	L	L	H	L	L
L	L	H	H	H	L	L	L	L	L	L	L	H	L
L	L	H	H	H	H	L	L	L	L	L	L	L	H

X: Don't Care

LOGIC DIAGRAM



This logic diagram has not be used to estimate propagation delays

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	-0.5 to +7.0	V
V_I	DC Input Voltage	-0.5 to +7.0	V
V_O	DC Output Voltage	-0.5 to V_{CC} + 0.5	V
I_{IK}	DC Input Diode Current	- 20	mA
I_{OK}	DC Output Diode Current	± 20	mA
I_O	DC Output Current	± 25	mA
I_{CC} or I_{GND}	DC V_{CC} or Ground Current	± 75	mA
T_{stg}	Storage Temperature	-65 to +150	°C
T_L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	2.0 to 5.5	V
V_I	Input Voltage	0 to 5.5	V
V_O	Output Voltage	0 to V_{CC}	V
T_{op}	Operating Temperature	-40 to +85	°C
dt/dv	Input Rise and Fall Time (see note 1) (V_{CC} = 3.3 ± 0.3V) (V_{CC} = 5.0 ± 0.5V)	0 to 100 0 to 20	ns/V ns/V

1) V_{IN} from 30% to 70% of V_{CC}

DC SPECIFICATIONS

Symbol	Parameter	Test Conditions		Value					Unit
		V_{CC} (V)		T_A = 25 °C			-40 to 85 °C		
				Min.	Typ.	Max.	Min.	Max.	
V_{IH}	High Level Input Voltage	2.0		1.5			1.5		V
		3.0 to 5.5		0.7V_{CC}			0.7V_{CC}		
V_{IL}	Low Level Input Voltage	2.0				0.5		0.5	V
		3.0 to 5.5				0.3V_{CC}		0.3V_{CC}	
V_{OH}	High Level Output Voltage	2.0	I_O=-50 µA	1.9	2.0		1.9		V
		3.0	I_O=-50 µA	2.9	3.0		2.9		
		4.5	I_O=-50 µA	4.4	4.5		4.4		
		3.0	I_O=-4 mA	2.58			2.48		
		4.5	I_O=-8 mA	3.94			3.8		
V_{OL}	Low Level Output Voltage	2.0	I_O=50 µA		0.0	0.1		0.1	V
		3.0	I_O=50 µA		0.0	0.1		0.1	
		4.5	I_O=50 µA		0.0	0.1		0.1	
		3.0	I_O=4 mA			0.36		0.44	
		4.5	I_O=8 mA			0.36		0.44	
I_I	Input Leakage Current	0 to 5.5	V_I = 5.5V or GND			±0.1		±1.0	µA
I_{CC}	Quiescent Supply Current	5.5	V_I = V_{CC} or GND			4		40	µA

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3$ ns)

Symbol	Parameter	Test Condition			Value					Unit
		V_{CC} (V)	C_L (pF)		T_A = 25 °C			-40 to 85 °C		
					Min.	Typ.	Max.	Min.	Max.	
t_{PLH} t_{PHL}	Propagation Delay Time A, B, C to Y	3.3(*)	15			8.0	12.3	1.0	14.5	ns
		3.3(*)	50			10.5	15.8	1.0	18.0	
		5.0(**)	15			5.5	8.1	1.0	9.5	
		5.0(**)	50			7.0	10.1	1.0	11.5	
t_{PLH} t_{PHL}	Propagation Delay Time G1 to Y	3.3(*)	15			8.1	12.8	1.0	15.0	ns
		3.3(*)	50			10.6	16.3	1.0	18.5	
		5.0(**)	15			5.4	8.1	1.0	9.5	
		5.0(**)	50			6.9	10.1	1.0	11.5	
t_{PLH} t_{PHL}	Propagation Delay Time $\overline{G2A}$, $\overline{G2B}$ to Y	3.3(*)	15			8.1	12.3	1.0	14.5	ns
		3.3(*)	50			10.6	15.8	1.0	18.0	
		5.0(**)	15			5.7	8.1	1.0	9.5	
		5.0(**)	50			7.2	10.1	1.0	11.5	

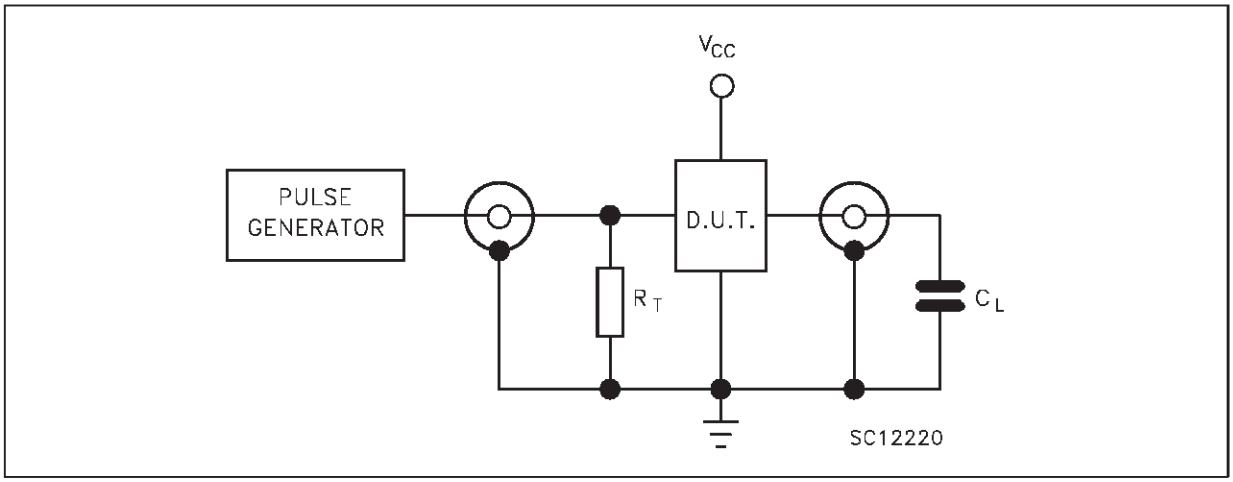
(*) Voltage range is 3.3V ± 0.3V
(**) Voltage range is 5V ± 0.5V

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Test Conditions	Value					Unit
			T_A = 25 °C			-40 to 85 °C		
			Min.	Typ.	Max.	Min.	Max.	
C_{IN}	Input Capacitance			4	10		10	pF
C_{PD}	Power Dissipation Capacitance (note 1)			37				pF

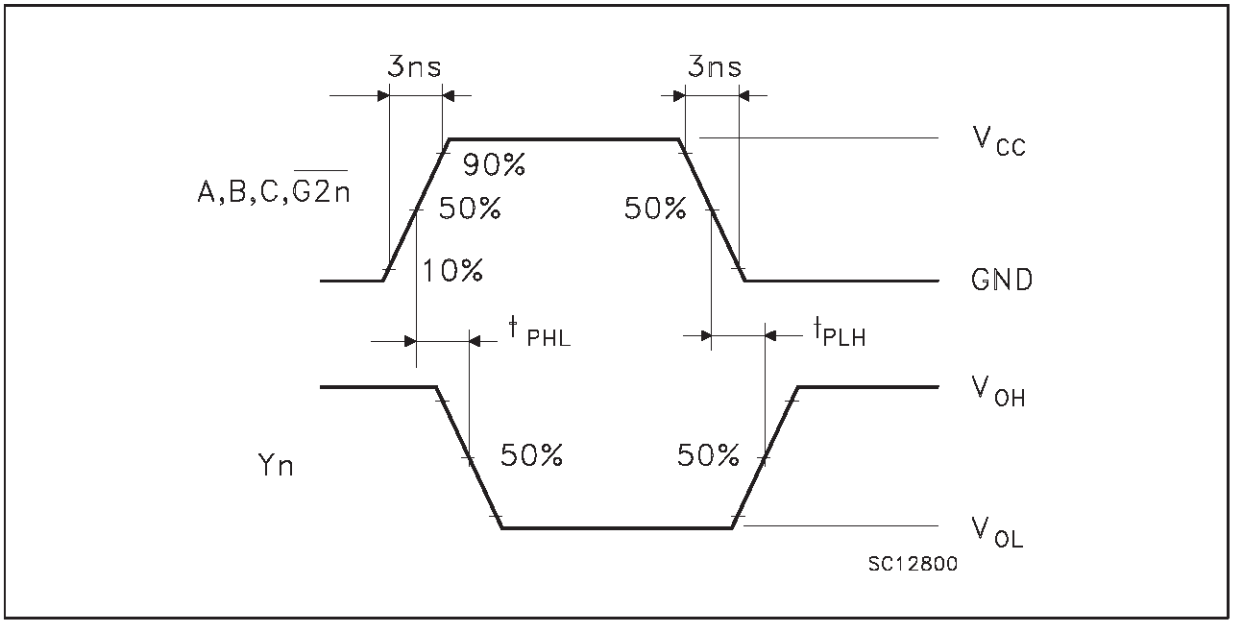
1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC}(opr) = C_{PD} \bullet V_{CC} \bullet f_{IN} + I_{CC}$

TEST CIRCUIT

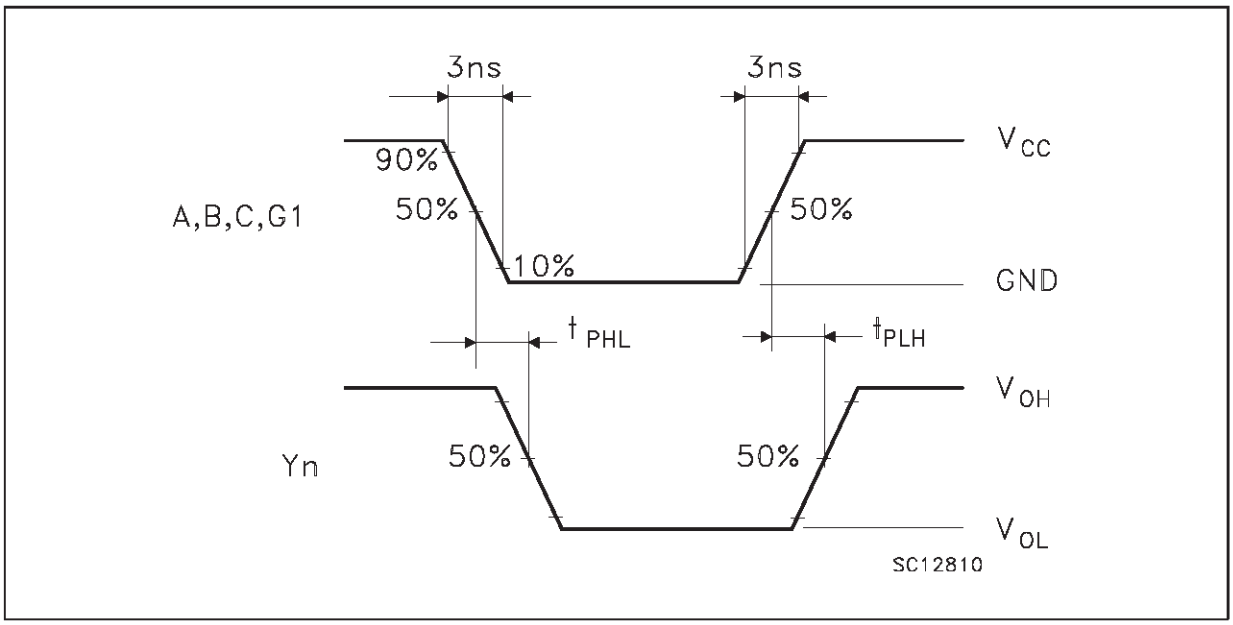


C_L = 15/50 pF or equivalent (includes jig and probe capacitance)
$R_L = R_1$ = 500Ω or equivalent
$R_T = Z_{OUT}$ of pulse generator (typically 50Ω)

WAVEFORM 1: PROPAGATION DELAYS FOR INVERTING OUTPUTS (f=1MHz; 50% duty cycle)

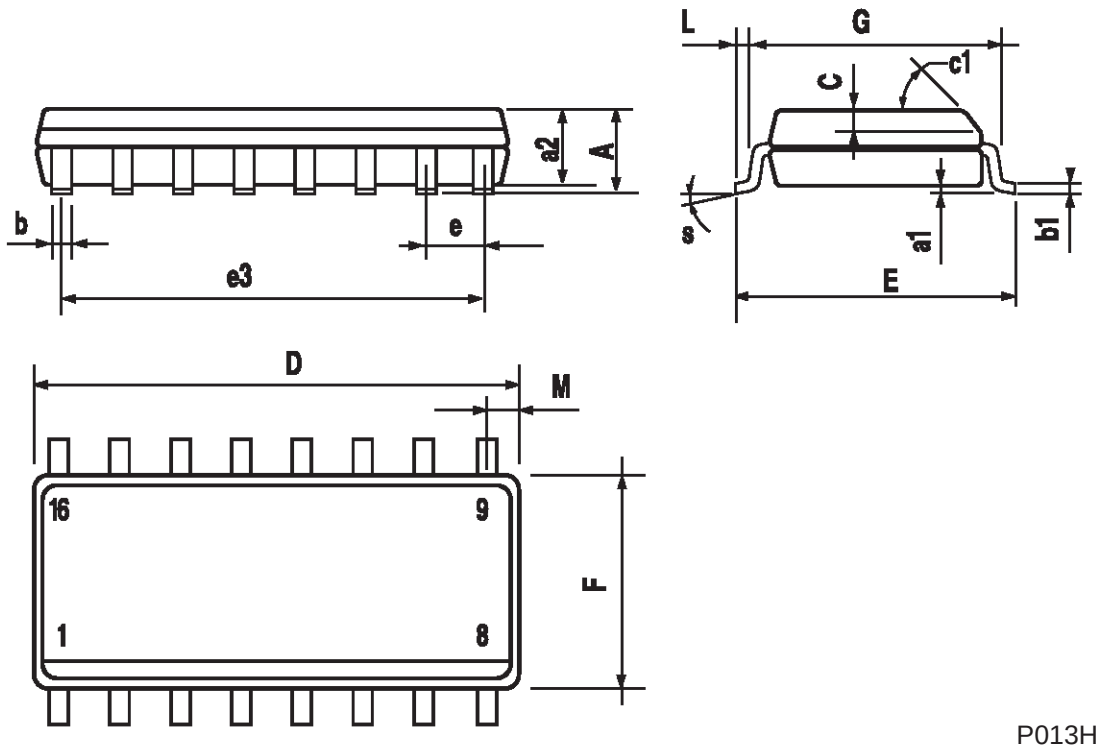


WAVEFORM 2: PROPAGATION DELAYS FOR NON-INVERTING OUTPUTS (f=1MHz; 50% duty cycle)



SO-16 MECHANICAL DATA

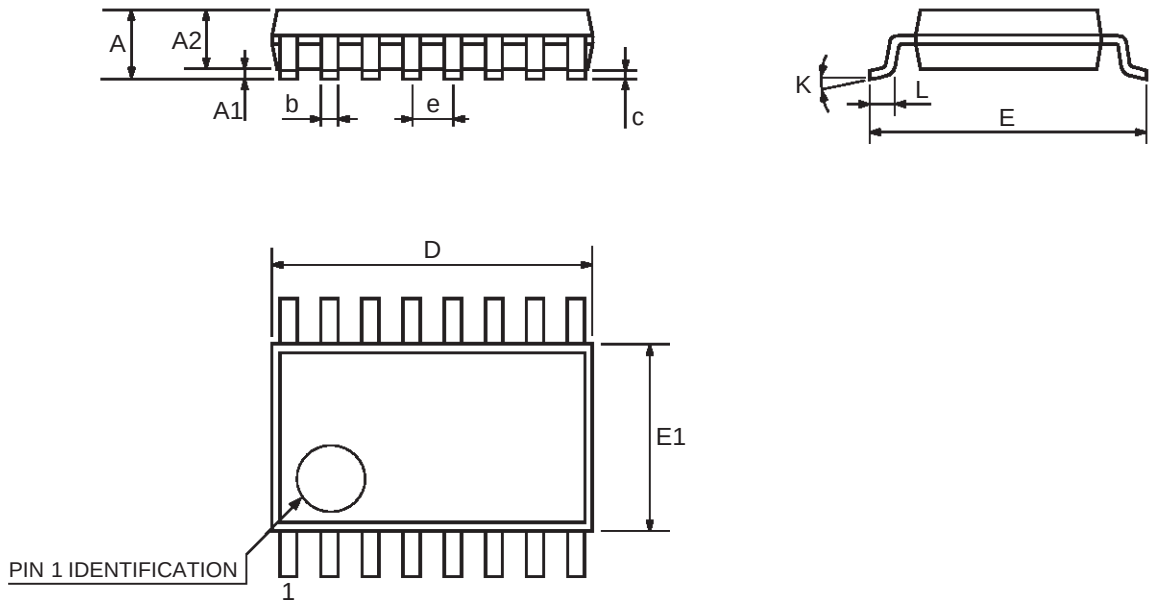
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.004		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45 (typ.)					
D	9.8		10	0.385		0.393
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		8.89			0.350	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.62			0.024
S	8 (max.)					



P013H

TSSOP16 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.1			0.433
A1	0.05	0.10	0.15	0.002	0.004	0.006
A2	0.85	0.9	0.95	0.335	0.354	0.374
b	0.19		0.30	0.0075		0.0118
c	0.09		0.20	0.0035		0.0079
D	4.9	5	5.1	0.193	0.197	0.201
E	6.25	6.4	6.5	0.246	0.252	0.256
E1	4.3	4.4	4.48	0.169	0.173	0.176
e		0.65 BSC			0.0256 BSC	
K	0^o	4^o	8^o	0^o	4^o	8^o
L	0.50	0.60	0.70	0.020	0.024	0.028



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